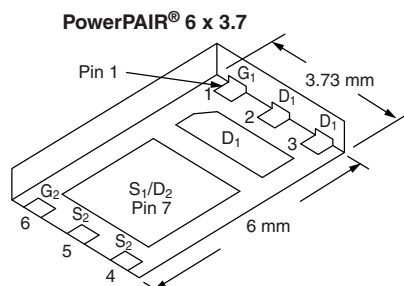


Dual N-Channel 30 V (D-S) MOSFETs with Schottky Diode

PRODUCT SUMMARY

	V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)
Channel-1	30	0.0093 at V _{GS} = 10 V	16 ^a	7.7 nC
		0.0130 at V _{GS} = 4.5 V	16 ^a	
Channel-2	30	0.0047 at V _{GS} = 10 V	35 ^a	17 nC
		0.0059 at V _{GS} = 4.5 V	35 ^a	



Ordering Information: SiZ790DT-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

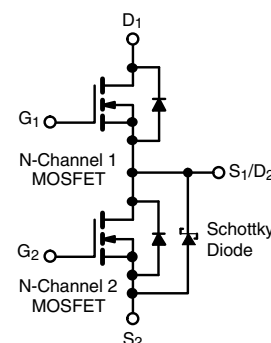
- Halogen-free According to IEC 61249-2-21 Definition
- SkyFET[®] Monolithic TrenchFET[®] Power MOSFETs and Schottky Diode
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- System Power
 - Notebook
 - Server
- POL
- Synchronous Buck Converter



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter		Symbol	Channel-1	Channel-2	Unit
Drain-Source Voltage		V _{DS}	30		V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current (T _J = 150 °C)	T _C = 25 °C	I _D	16 ^a	35 ^a	A
	T _C = 70 °C		16 ^a	35 ^a	
	T _A = 25 °C		12.9 ^{b, c}	23.4 ^{b, c}	
	T _A = 70 °C		10.3 ^{b, c}	18.7 ^{b, c}	
Pulsed Drain Current (t = 300 μs)		I _{DM}	70	100	
Continuous Source Drain Diode Current	T _C = 25 °C	I _S	16 ^a	35 ^a	
	T _A = 25 °C		3.2 ^{b, c}	3.8 ^{b, c}	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	16	30	
Single Pulse Avalanche Energy		E _{AS}	13	45	mJ
Maximum Power Dissipation	T _C = 25 °C	P _D	27	48	W
	T _C = 70 °C		17	31	
	T _A = 25 °C		3.9 ^{b, c}	4.6 ^{b, c}	
	T _A = 70 °C		2.5 ^{b, c}	3 ^{b, c}	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature) ^{d, e}			260		

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Channel-1		Channel-2		Unit
		Typ.	Max.	Typ.	Max.	
Maximum Junction-to-Ambient ^{b, f}	R _{thJA}	24	32	20	27	°C/W
Maximum Junction-to-Case (Drain)	R _{thJC}	3.5	4.6	2	2.6	

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c. t = 10 s.

d. See solder profile (www.vishay.com/doc?73257). The PowerPAIR is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under steady state conditions is 67 °C/W for channel-1 and 65 °C/W for channel-2.

SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Conditions		Min.	Typ.	Max.	Unit	
Static								
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	Ch-1	30			V	
		V _{GS} = 0 V, I _D = 250 μA	Ch-2	30				
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	Ch-1	1		2.2		
		V _{DS} = V _{GS} , I _D = 250 μA	Ch-2	1.1		2.2		
Gate Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	Ch-1 Ch-2			± 100 ± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	Ch-1			1	μA	
		V _{DS} = 30 V, V _{GS} = 0 V	Ch-2		50	200		
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C	Ch-1			5		
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C	Ch-2		140	1400		
On-State Drain Current ^b	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	Ch-1	15			A	
		V _{DS} ≥ 5 V, V _{GS} = 10 V	Ch-2	20				
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 15 A	Ch-1		0.0075	0.0093	Ω	
		V _{GS} = 10 V, I _D = 20 A	Ch-2		0.0038	0.0047		
		V _{GS} = 4.5 V, I _D = 13 A	Ch-1		0.0105	0.0130		
		V _{GS} = 4.5 V, I _D = 20 A	Ch-2		0.0048	0.0059		
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 15 A	Ch-1		48		S	
		V _{DS} = 15 V, I _D = 20 A	Ch-2		85			
Dynamic ^a								
Input Capacitance	C _{iss}	Channel-1 V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	Ch-1 Ch-2		830 1980		pF	
Output Capacitance	C _{oss}		Ch-1 Ch-2		185 455			
Reverse Transfer Capacitance	C _{rss}	Channel-2 V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	Ch-1 Ch-2		80 165			
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 15 A	Ch-1		15.6	24	nC	
		V _{DS} = 15 V, V _{GS} = 10 V, I _D = 20 A	Ch-2		36	54		
		Channel-1 V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 15 A	Ch-1 Ch-2		7.7 17	12 26		
			Channel-2 V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 20 A	Ch-1 Ch-2		2.6 5.7		
Gate-Source Charge	Q _{gs}							
Gate-Drain Charge	Q _{gd}							
Gate Resistance	R _g	f = 1 MHz	Ch-1 Ch-2	0.2 0.2	1 0.9	2 1.8		Ω

Notes:

a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.



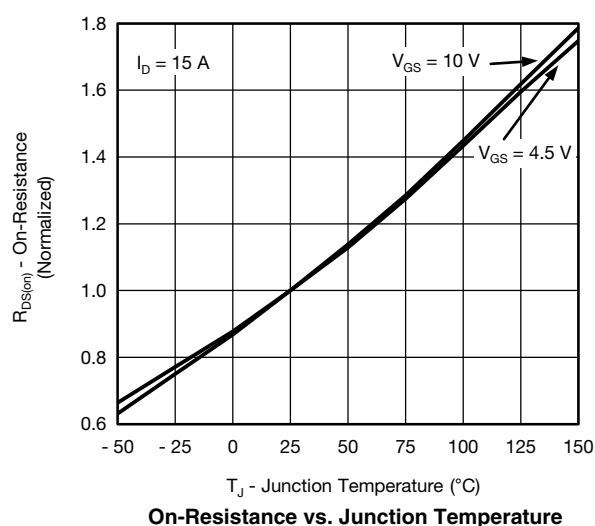
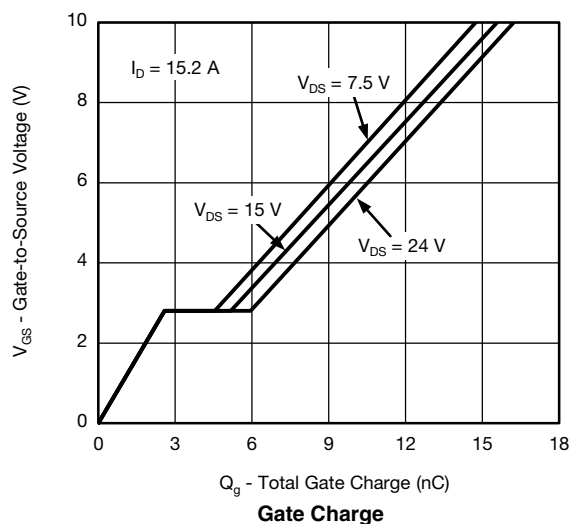
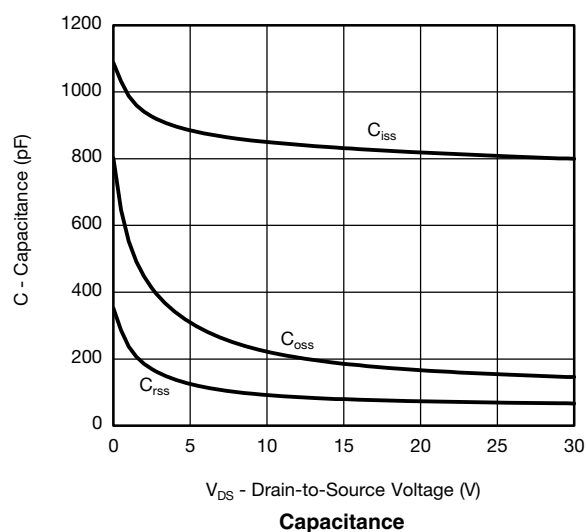
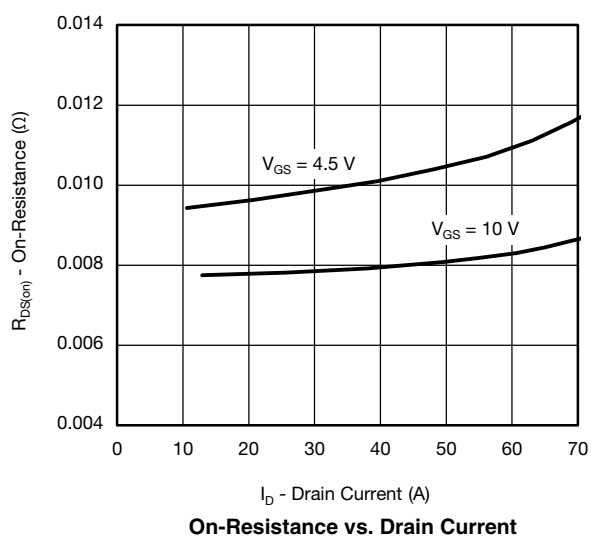
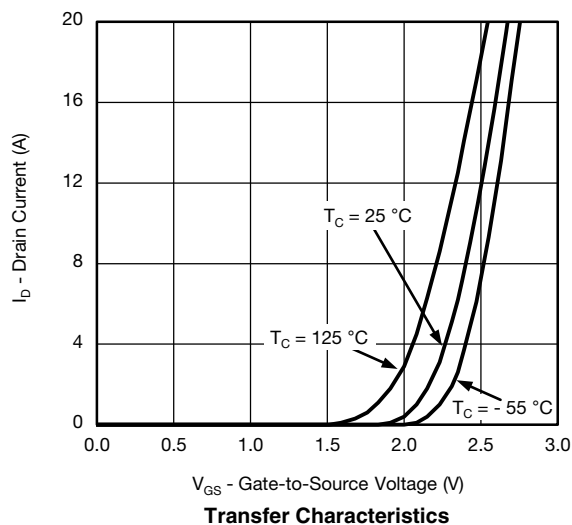
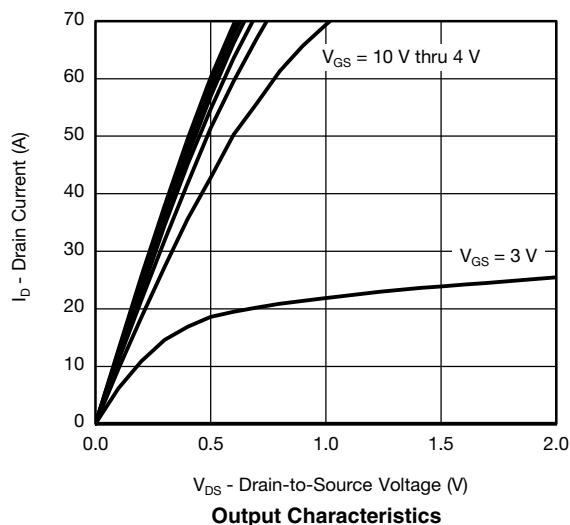
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Dynamic ^a							
Turn-On Delay Time	t _{d(on)}	Channel-1 V _{DD} = 15 V, R _L = 1.5 Ω I _D ≅ 10 A, V _{GEN} = 4.5 V, R _g = 1 Ω	Ch-1		10	20	ns
			Ch-2		20	40	
Rise Time	t _r		Ch-1		15	30	
			Ch-2		15	30	
Turn-Off Delay Time	t _{d(off)}	Channel-2 V _{DD} = 15 V, R _L = 1.5 Ω I _D ≅ 10 A, V _{GEN} = 4.5 V, R _g = 1 Ω	Ch-1		15	30	
			Ch-2		25	50	
Fall Time	t _f		Ch-1		7	15	
			Ch-2		10	20	
Turn-On Delay Time	t _{d(on)}	Channel-1 V _{DD} = 15 V, R _L = 1.5 Ω I _D ≅ 10 A, V _{GEN} = 10 V, R _g = 1 Ω	Ch-1		5	10	
			Ch-2		10	20	
Rise Time	t _r		Ch-1		15	30	
			Ch-2		10	20	
Turn-Off Delay Time	t _{d(off)}	Channel-2 V _{DD} = 15 V, R _L = 1.5 Ω I _D ≅ 10 A, V _{GEN} = 10 V, R _g = 1 Ω	Ch-1		17	35	
			Ch-2		25	50	
Fall Time	t _f		Ch-1		7	15	
			Ch-2		10	20	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	Ch-1			16	A
			Ch-2			35	
Pulse Diode Forward Current ^a	I _{SM}		Ch-1			70	
			Ch-2			100	
Body Diode Voltage	V _{SD}	I _S = 10 A, V _{GS} = 0 V	Ch-1		0.8	1.2	V
		I _S = 2 A, V _{GS} = 0 V	Ch-2		0.38	0.48	
Body Diode Reverse Recovery Time	t _{rr}	Channel-1 I _F = 10 A, dI/dt = 100 A/μs, T _J = 25 °C	Ch-1		15	30	ns
			Ch-2		20	40	
Body Diode Reverse Recovery Charge	Q _{rr}		Ch-1		6	12	nC
			Ch-2		15	32	
Reverse Recovery Fall Time	t _a	Channel-2 I _F = 10 A, dI/dt = 100 A/μs, T _J = 25 °C	Ch-1		9		ns
			Ch-2		10.5		
Reverse Recovery Rise Time	t _b		Ch-1		6		
			Ch-2		9.5		

Notes:

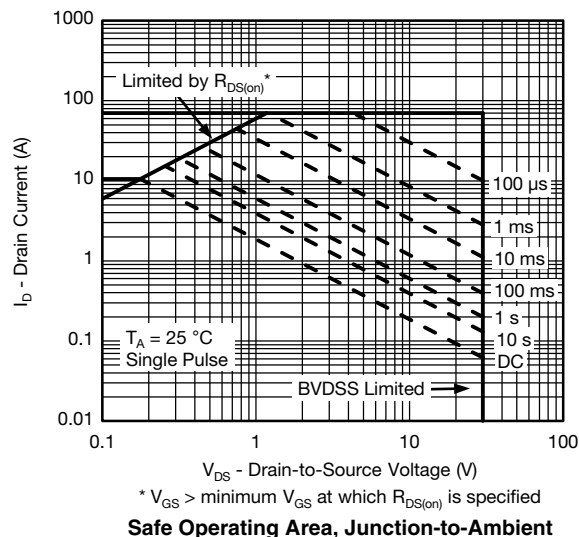
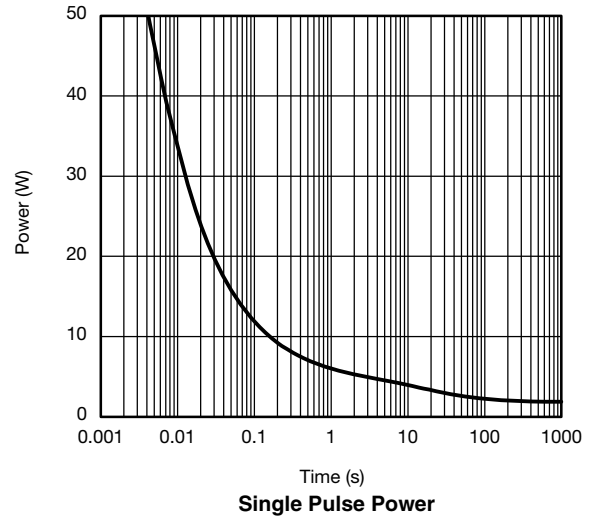
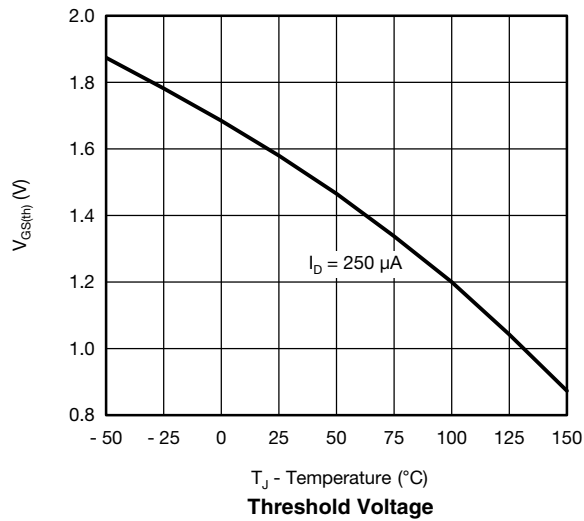
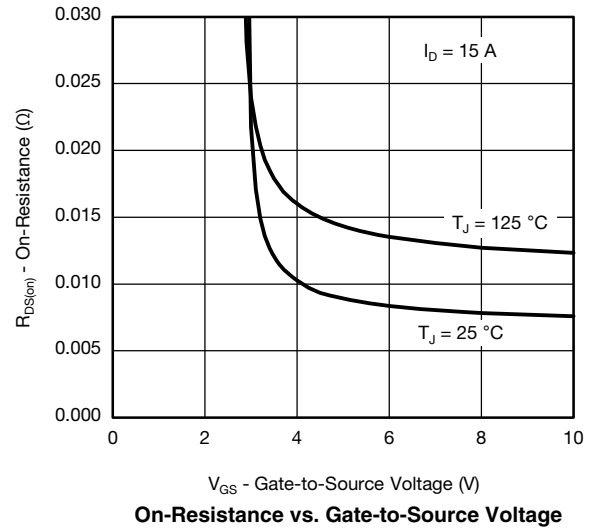
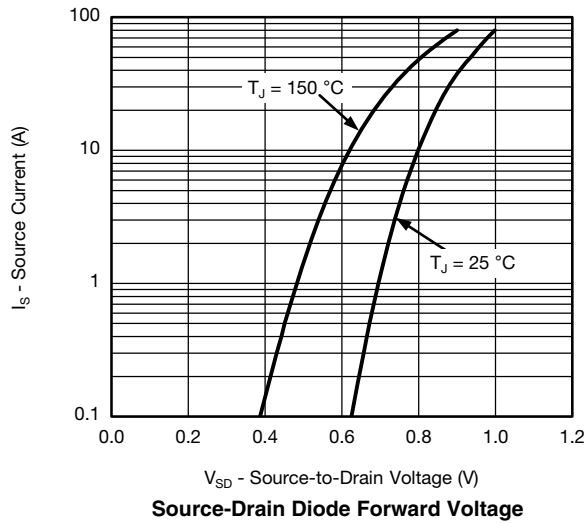
a. Guaranteed by design, not subject to production testing.

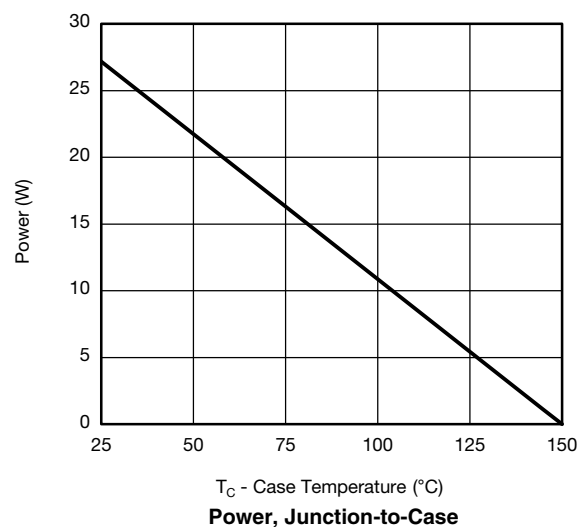
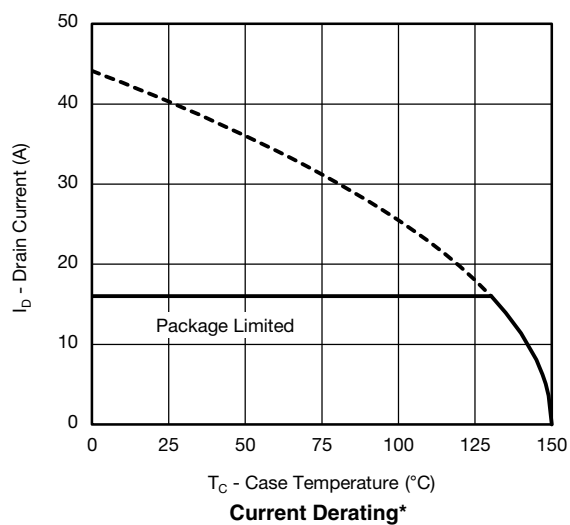
b. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

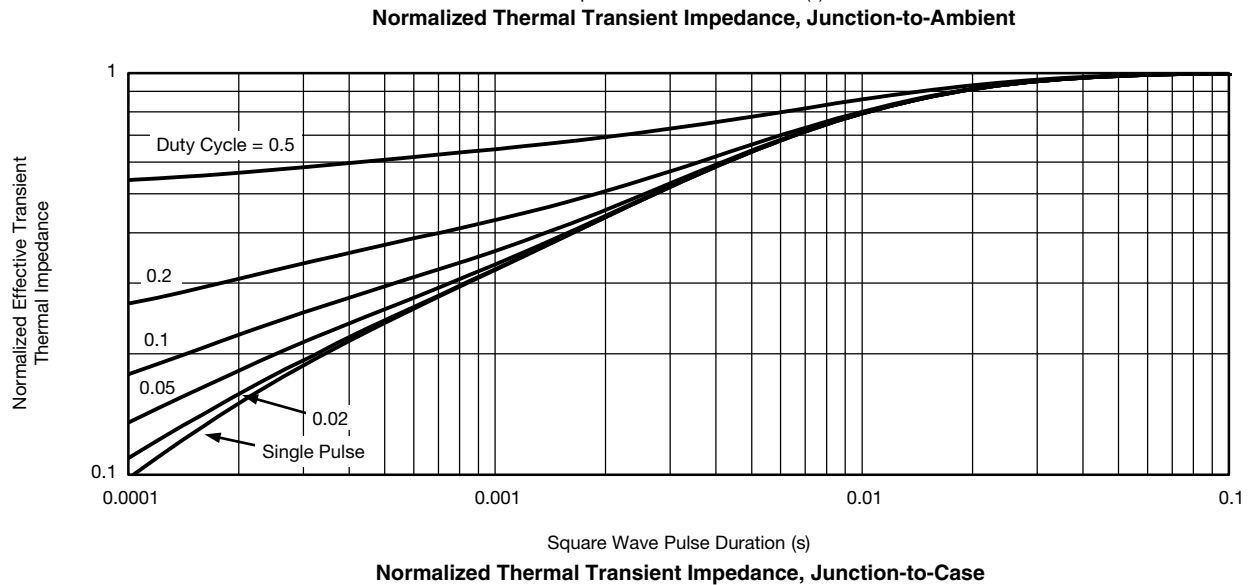
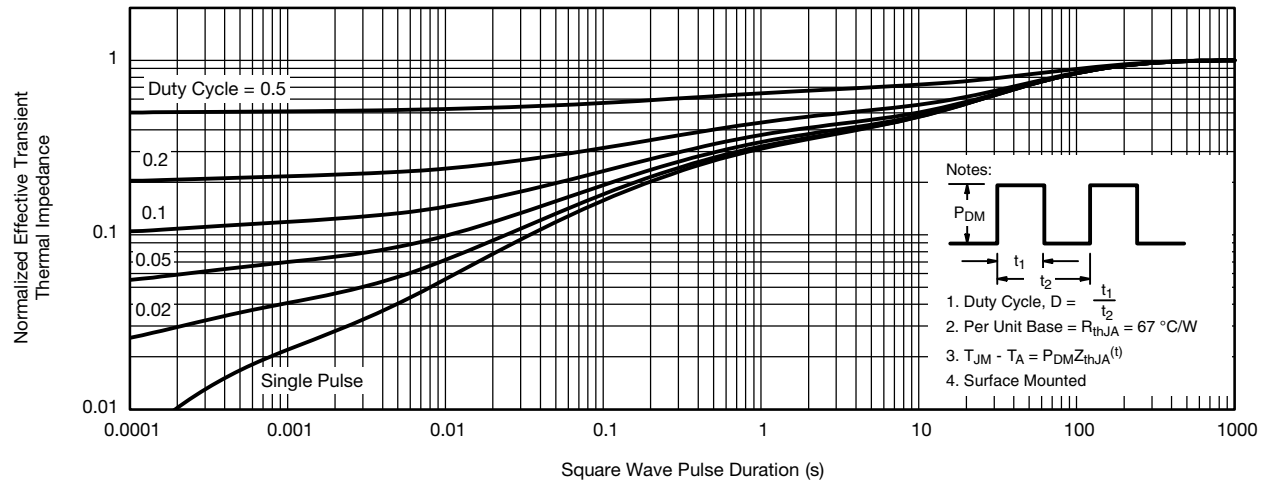
CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

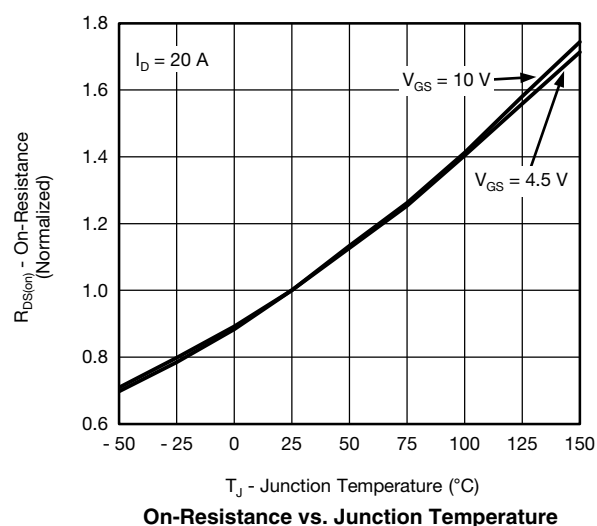
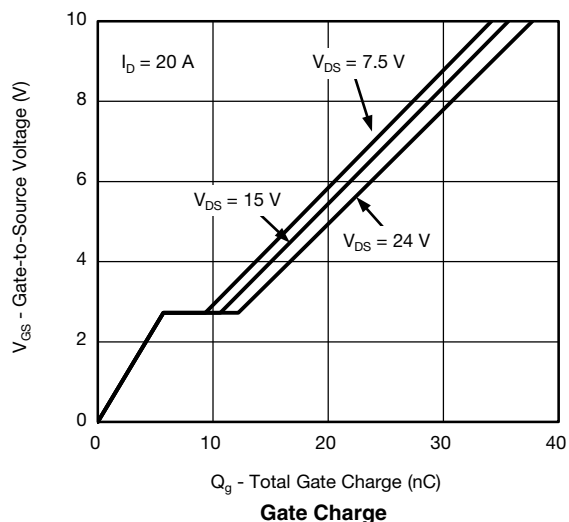
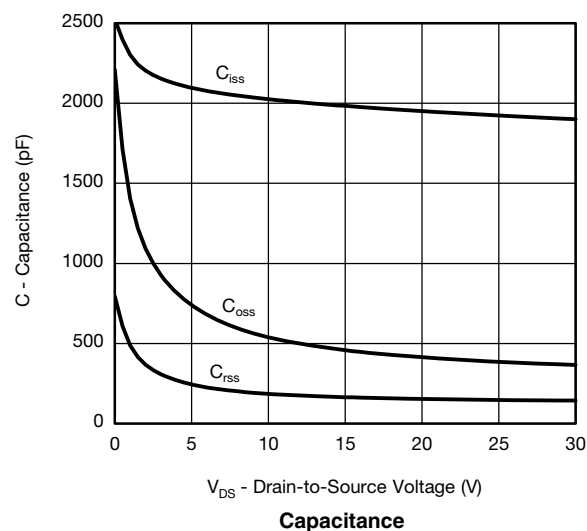
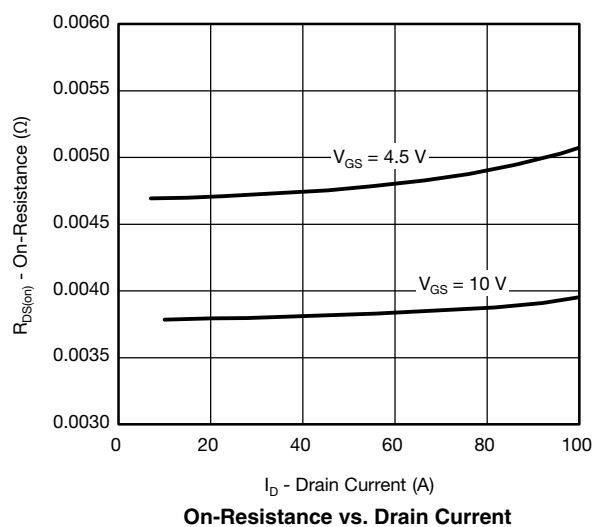
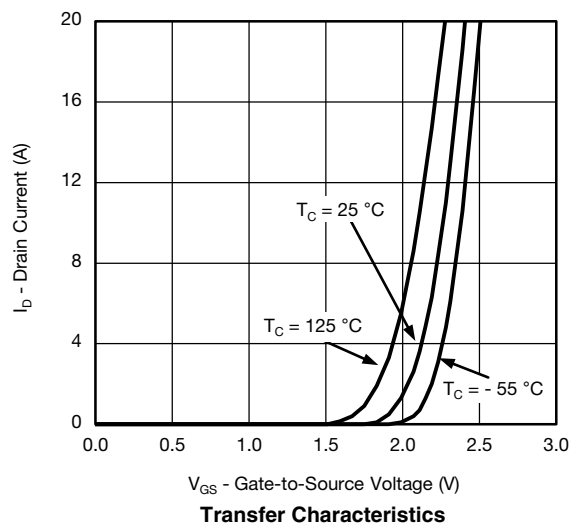
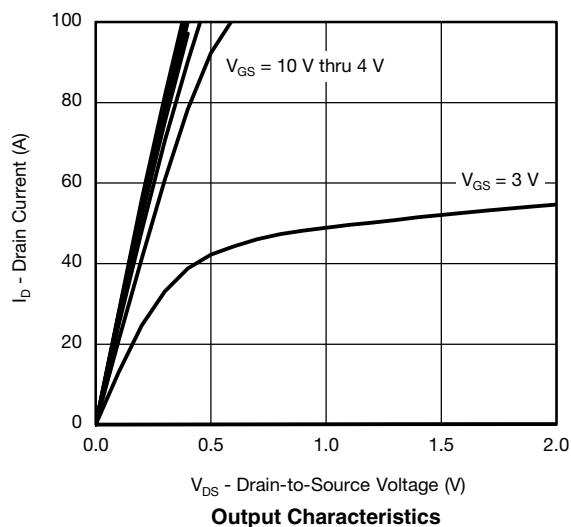


CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

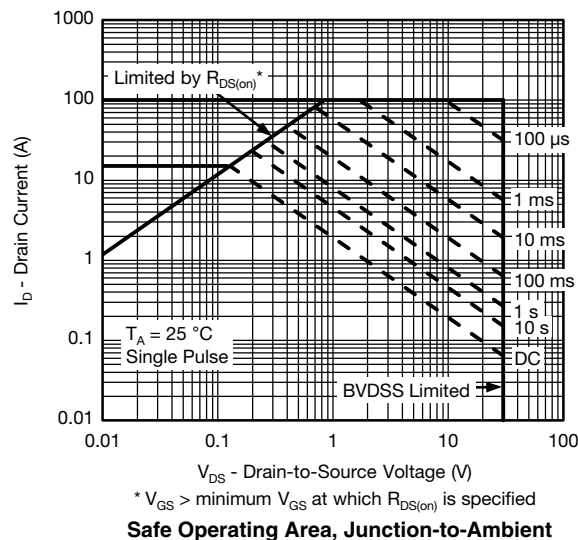
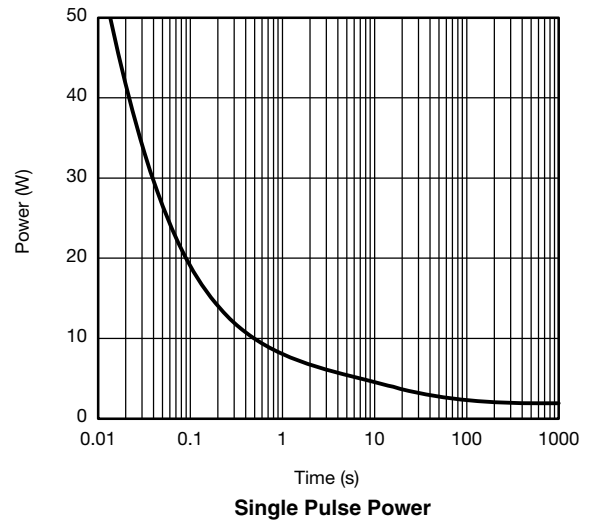
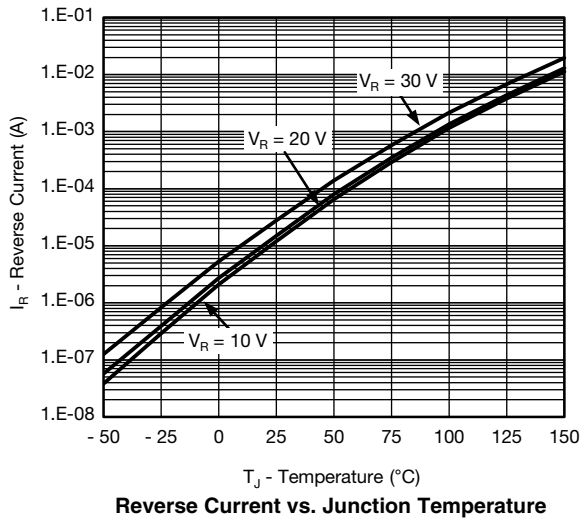
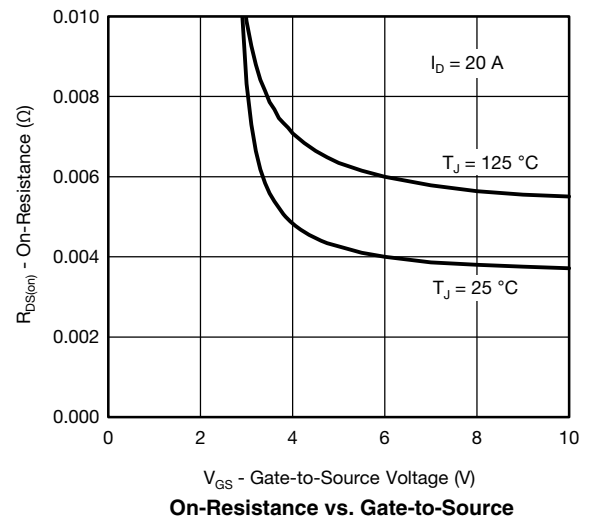
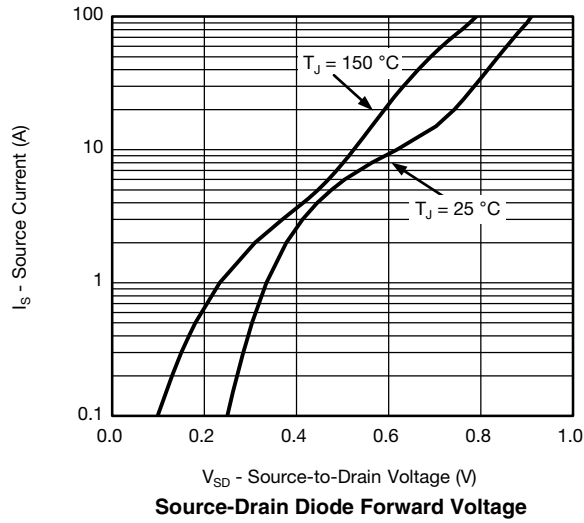
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

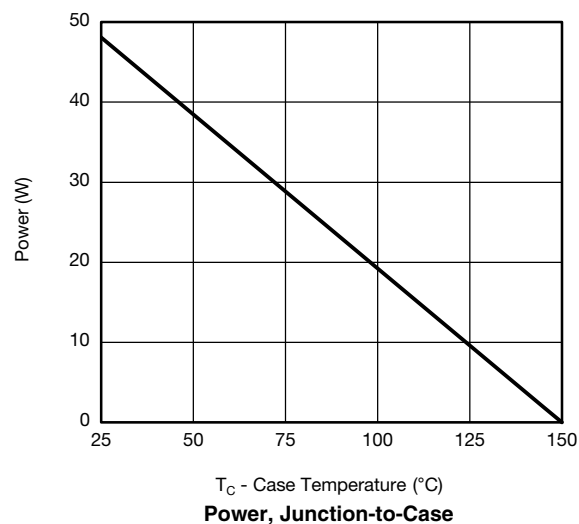
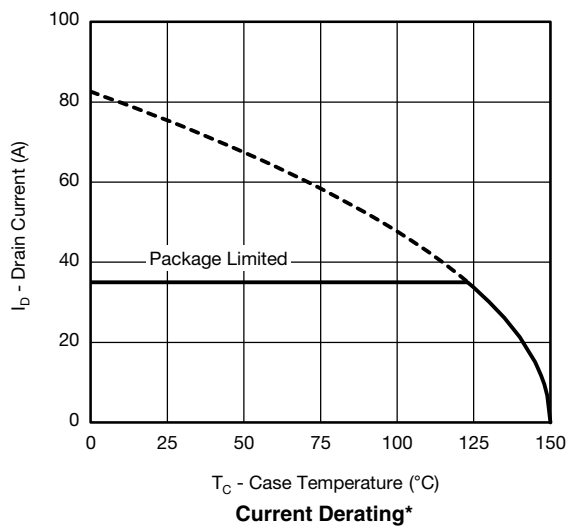
CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

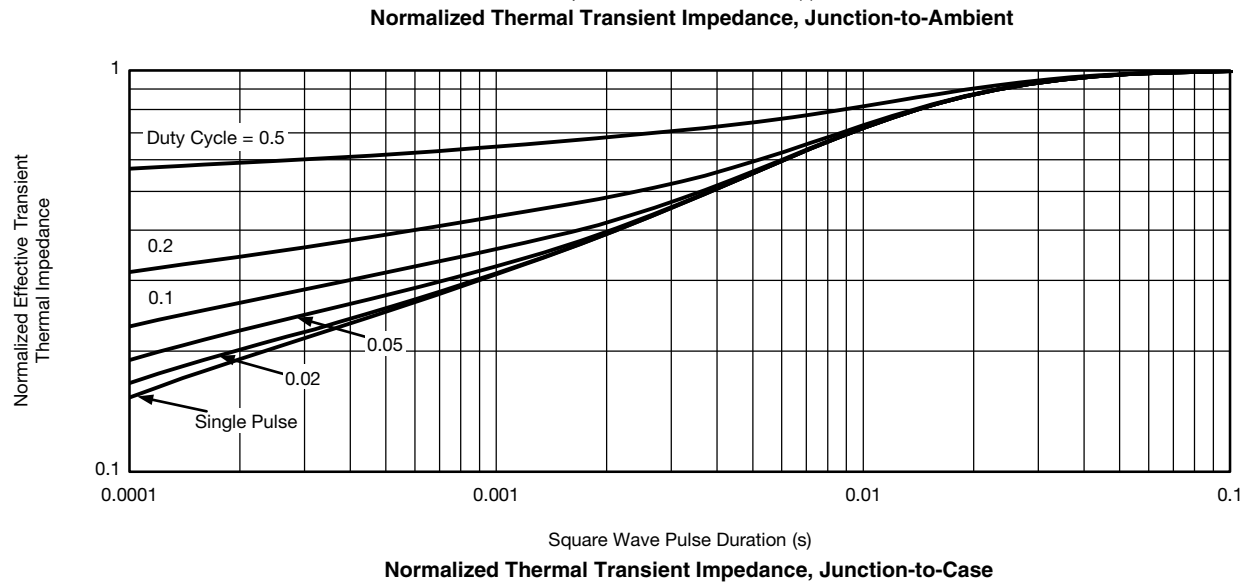
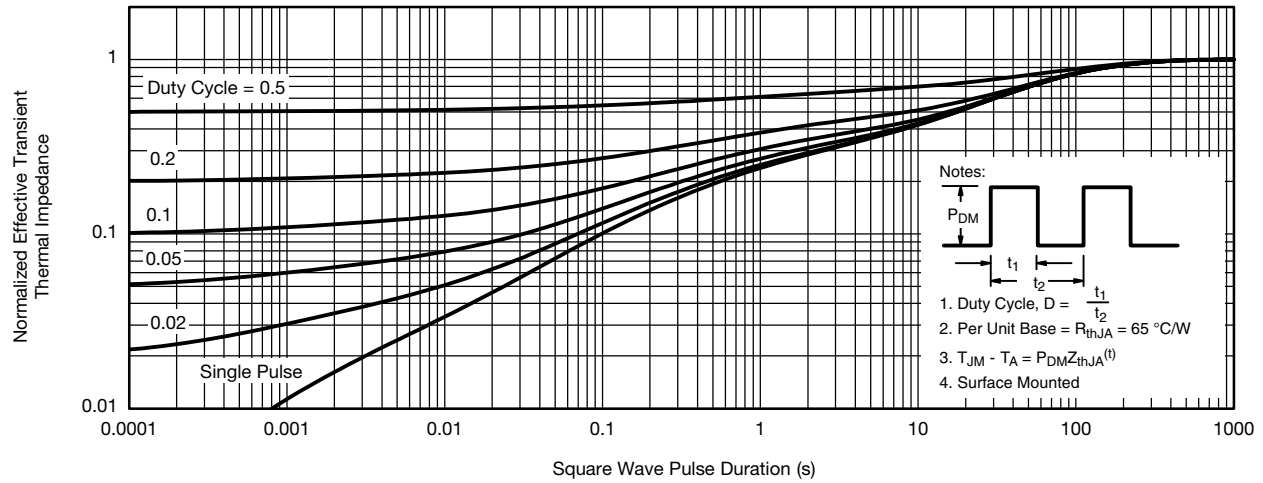
CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

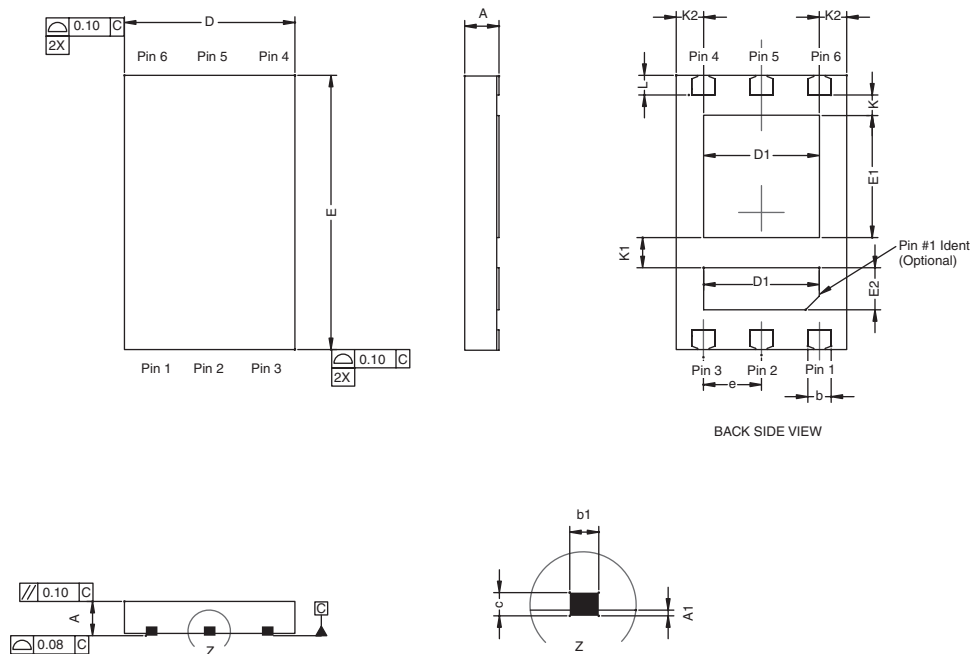
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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PowerPAIR™ 6 x 3.7 CASE OUTLINE



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.70	0.75	0.80	0.028	0.030	0.032
A1	0.00	-	0.05	0.000	-	0.002
b	0.46	0.51	0.56	0.018	0.020	0.022
b1	0.20	0.25	0.38	0.008	0.010	0.015
C	0.18	0.20	0.23	0.007	0.008	0.009
D	3.65	3.73	3.81	0.144	0.147	0.150
D1	2.41	2.53	2.65	0.095	0.100	0.104
E	5.92	6.00	6.08	0.233	0.236	0.239
E1	2.62	2.67	2.72	0.103	0.105	0.107
E2	0.87	0.92	0.97	0.034	0.036	0.038
e	1.27 BSC			0.05 BSC		
K	0.45 TYP.			0.018 TYP.		
K1	0.66 TYP.			0.026 TYP.		
K2	0.60 TYP.			0.024 TYP.		
L	0.38	0.43	0.48	0.015	0.017	0.019
ECN: S-82772-Rev. B, 17-Nov-08 DWG: 5979						

Technical drawing of a mechanical part, showing dimensions in inches and millimeters. The drawing includes a top view and a side view, with a large dimension of 0.4390 (11.151) indicated on the right side.

Key dimensions and tolerances:

- Overall width: 0.3520 (8.941)
- Overall height: 0.4390 (11.151)
- Top view dimensions:
 - Top edge: 0.0220 (0.559)
 - Right edge: 0.0190 (0.483)
 - Center hole diameter: 0.1040 (2.642)
 - Center hole position: 0, 0.11
 - Center hole diameter: 0, 0.03
 - Center hole position: 0, 0
- Side view dimensions:
 - Top edge: 0.0170 (0.432)
 - Bottom edge: 0.0170 (0.432)
 - Left edge: 0.0220 (0.559)
 - Right edge: 0.0380 (0.965)
 - Center hole diameter: 0.1070 (2.718)
 - Center hole position: 0, -0.0645
- Bottom view dimensions:
 - Bottom edge: 0.0500 (1.27)
 - Left edge: -0.05, -0.11
 - Center hole diameter: 0, -0.11

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